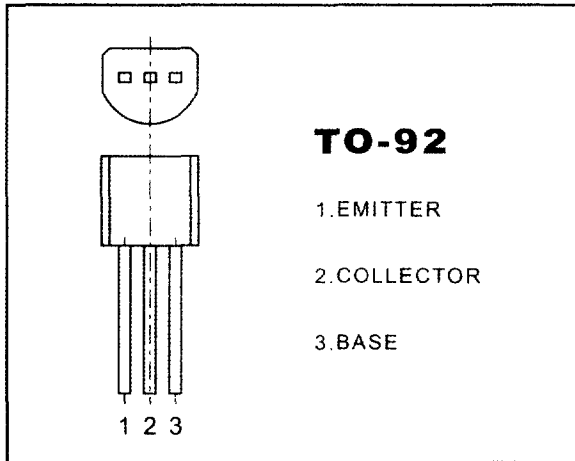


TO-92 Plastic-Encapsulate Transistors

A733 TRANSISTOR(PNP)



FEATURES

Power dissipation

P_{CM} : 0.25W ($T_{amb}=25^{\circ}C$)

Collector current

I_{CM} : -0.15A

Collector-base voltage

$V_{(BR)CBO}$: -60 V

Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$

ELECTRICAL CHARACTERISTICS

($T_{amb}=25^{\circ}C$ unless otherwise specified)

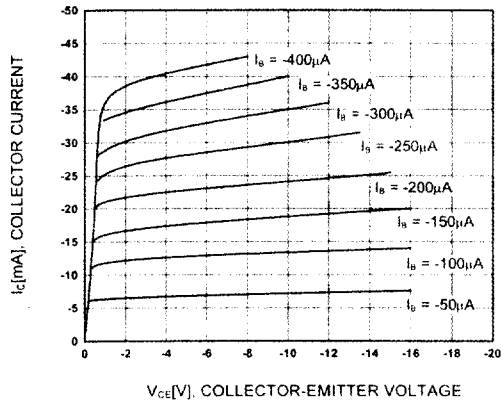
Parameter	Symbol	Test conditions	Min.	Typ.	Max.	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -5 \mu A, I_E = 0$	-60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1 mA, I_B = 0$	-50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -50 \mu A, I_C = 0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB} = -60 V, I_E = 0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5 V, I_C = 0$			-0.1	μA
DC current gain	h_{FE}	$V_{CE} = -6 V, I_C = -1 mA$	90	200	600	
Collector-emitter saturation voltage	V_{CEsat}	$I_C = -100 mA, I_B = -10 mA$		-0.18	-0.3	V
Transition frequency	f_T	$V_{CE} = -6 V, I_C = -10 mA$ $f = 30 MHz$	50	180		MHz

CLASSIFICATION OF h_{FE}

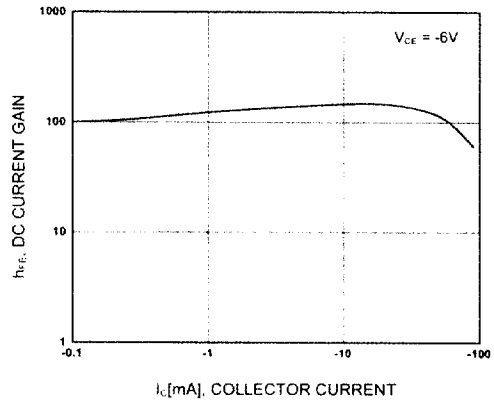
Rank	R	Q	P	K
Range	90-180	135-270	200-400	300-600

Typical Characteristics

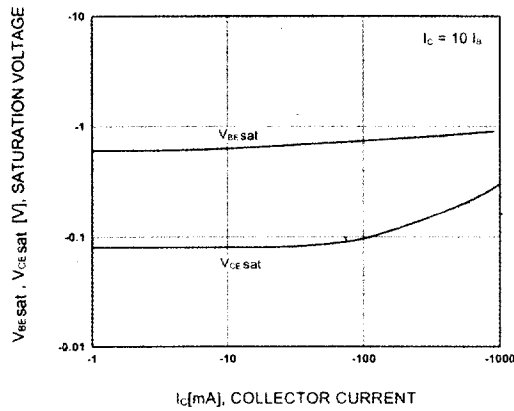
A733



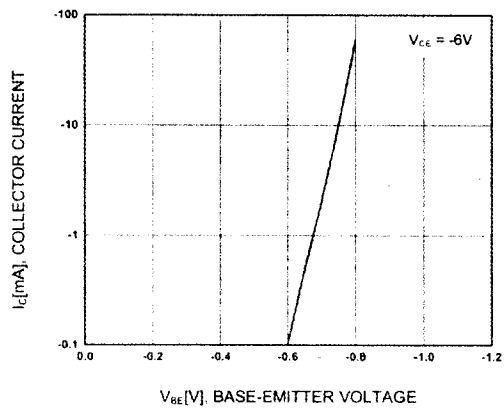
Static Characteristic



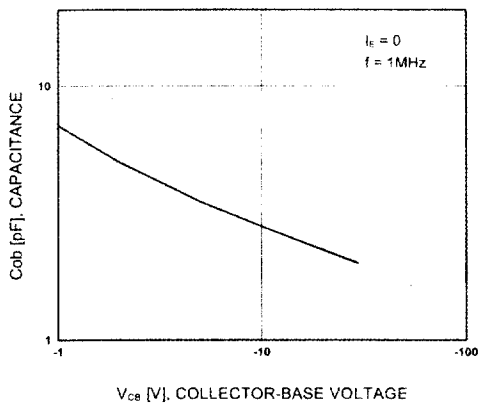
DC current Gain



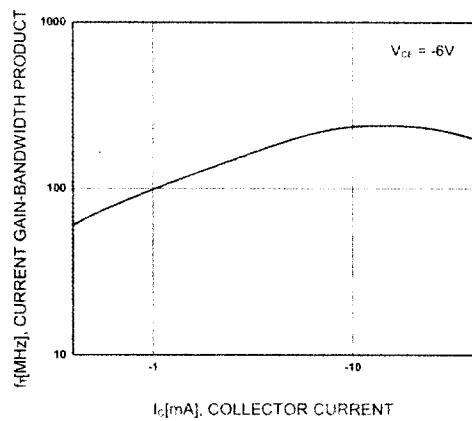
Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage



Base-Emitter On Voltage



Collector Output Capacitance



Current Gain Bandwidth Product